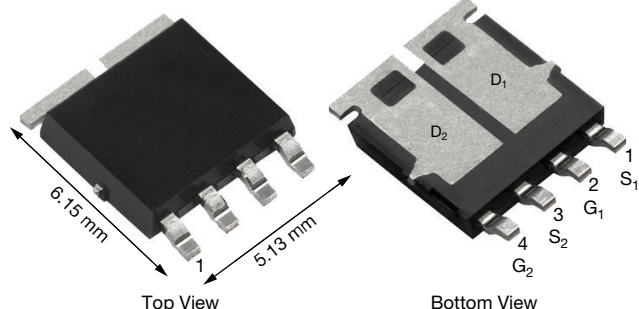
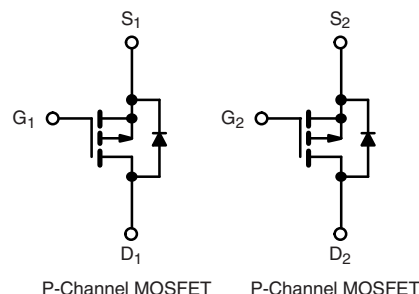


Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L Dual


FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE


PRODUCT SUMMARY	
V _{DS} (V)	- 30
R _{DS(on)} (Ω) at V _{GS} = - 10 V	0.017
R _{DS(on)} (Ω) at V _{GS} = - 4.5 V	0.036
I _D (A)	- 30
Configuration	Dual

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ951EP (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	- 30	V	
Gate-source voltage	V _{GS}	± 20		
Continuous drain current	I _D	- 30	A	
		- 28		
Continuous source current (diode conduction) ^a	I _S	- 30		
Pulsed drain current ^b	I _{DM}	- 120		
Single pulse avalanche current	I _{AS}	- 27		
Single pulse avalanche energy	E _{AS}	36.5	mJ	
Maximum power dissipation ^b	P _D	56	W	
		18.5		
Operating junction and storage temperature range	T _J , T _{stg}	- 55 to + 175	°C	
Soldering recommendations (peak temperature) ^{e, f}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R _{thJA}	85	°C/W	
Junction-to-case (drain)	R _{thJC}	2.7		

Notes

- Package limited
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- Parametric verification ongoing
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

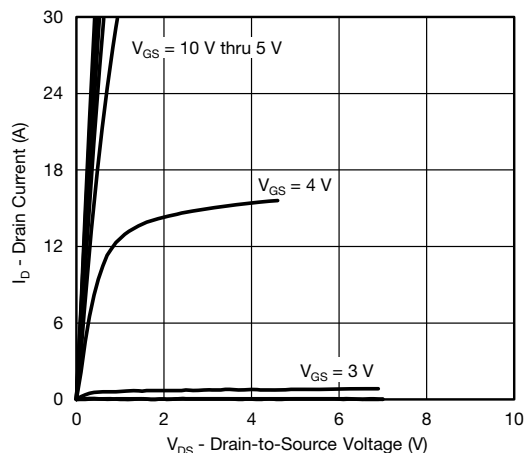
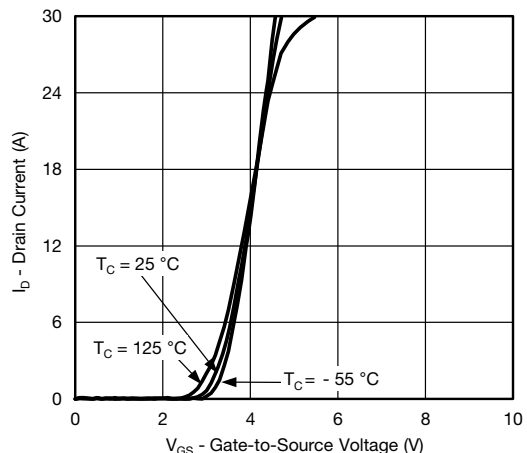
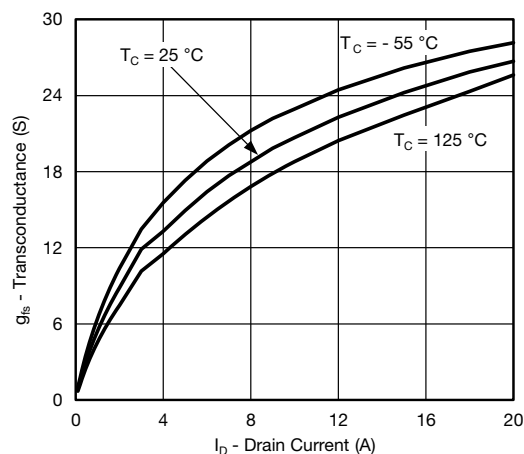
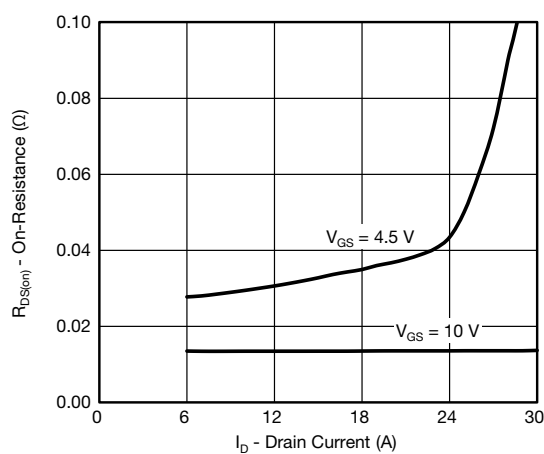
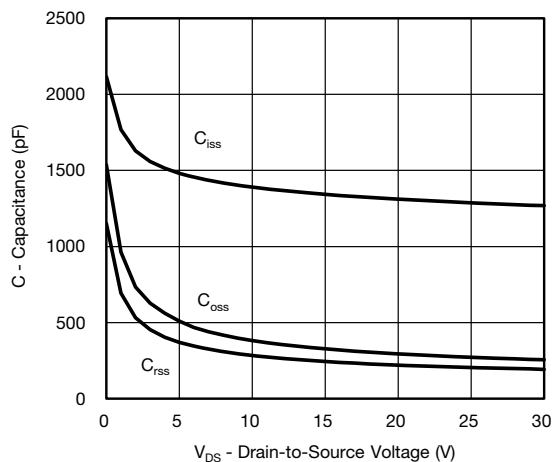
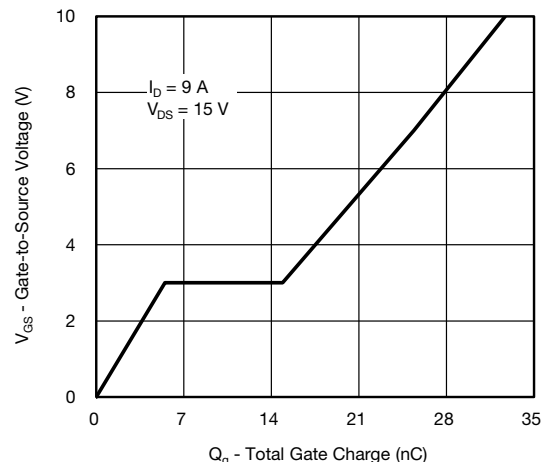


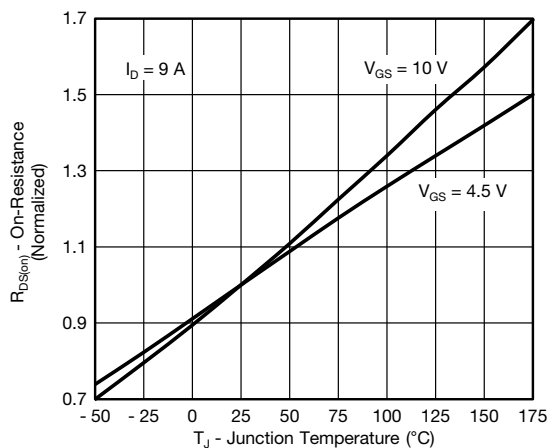
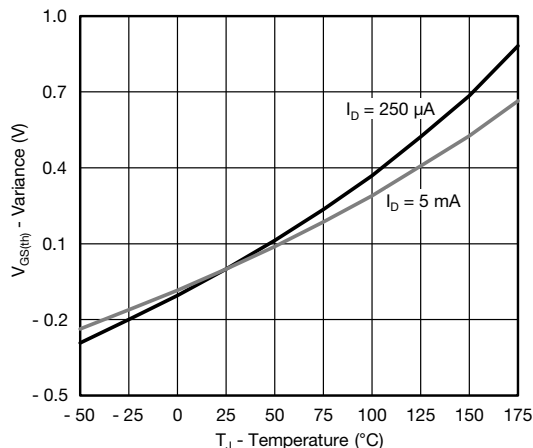
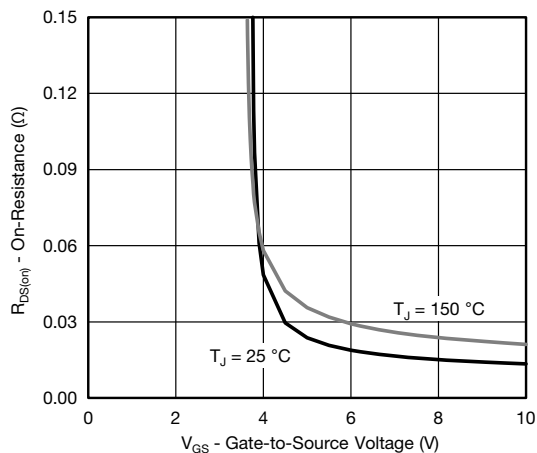
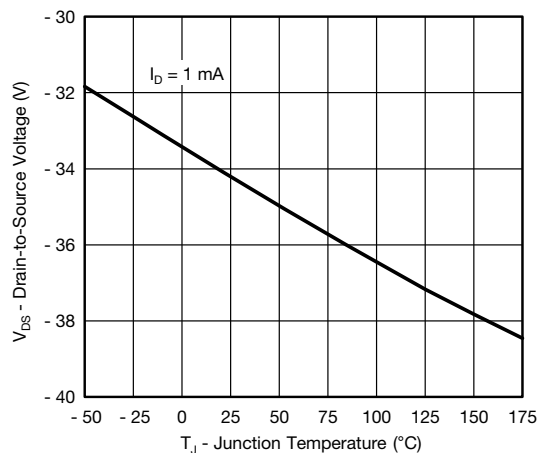
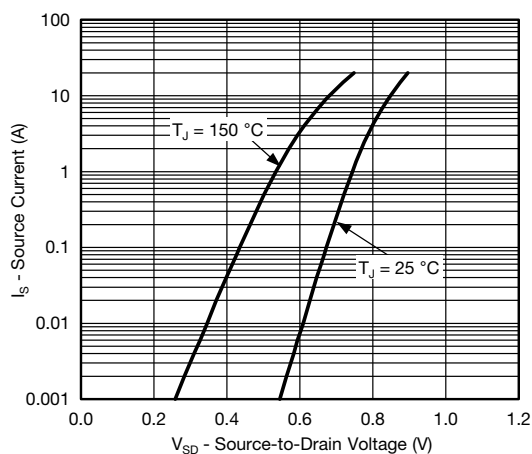
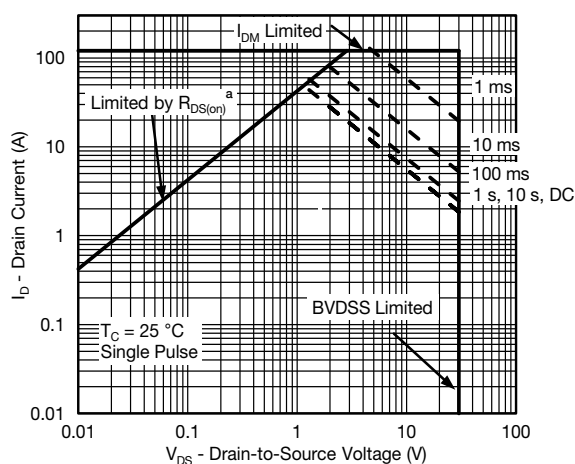
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 30	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA		- 1.5	- 2.0	- 2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 30 V	-	-	- 1	μA
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-state drain current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} = - 5 V	- 30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 7.5 A	-	0.014	0.017	Ω
		V _{GS} = - 10 V	I _D = - 7.5A, T _J = 125 °C	-	-	0.034	
		V _{GS} = - 10 V	I _D = - 7.5 A, T _J = 175 °C	-	-	0.039	
		V _{GS} = - 4.5 V	I _D = - 5 A	-	0.030	0.036	
Forward transconductance ^b	g _{fs}	V _{DS} = - 15 V, I _D = - 7.5 A		-	18	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = - 10 V, f = 1 MHz	-	1345	1680	pF
Output capacitance	C _{oss}			-	330	415	
Reverse transfer capacitance	C _{rss}			-	245	305	
Total gate charge ^c	Q _g	V _{GS} = - 10 V	V _{DS} = - 15 V, I _D = - 9 A	-	33	50	nC
Gate-source charge ^c	Q _{gs}			-	5.5	-	
Gate-drain charge ^c	Q _{gd}			-	9.4	-	
Gate resistance	R _g	f = 1 MHz		3	6.31	10.5	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.66 Ω I _D ≅ - 9 A, V _{GEN} = - 10 V, R _g = 6 Ω		-	12	18	ns
Rise time ^c	t _r			-	12	18	
Turn-off delay time ^c	t _{d(off)}			-	39	59	
Fall time ^c	t _f			-	28	42	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	- 120	A
Forward voltage	V _{SD}	I _F = - 4.5 A, V _{GS} = 0		-	- 0.8	- 1.2	V

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

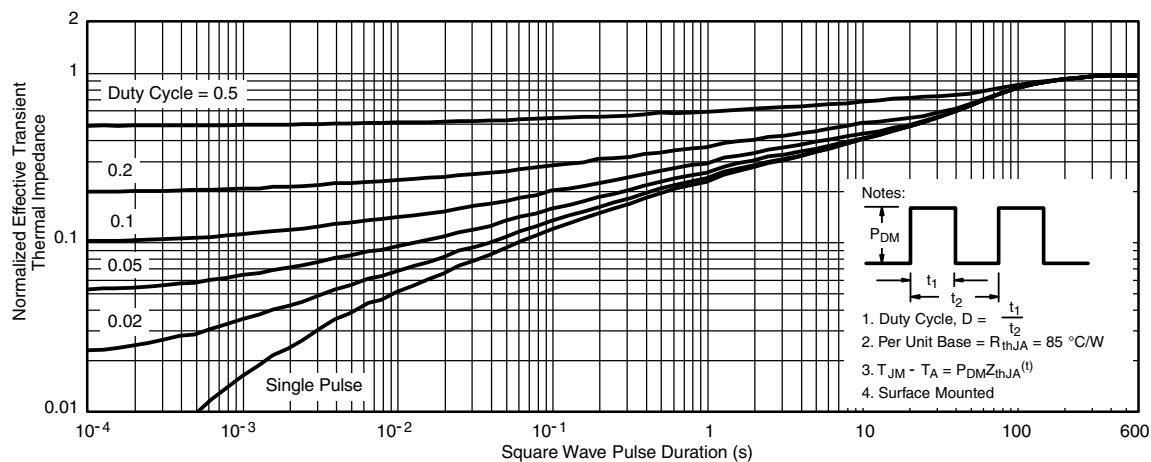
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


On-Resistance vs. Junction Temperature

Threshold Voltage

On-Resistance vs. Gate-to-Source Voltage

BVDSS vs. Junction Temperature

Source Drain Diode Forward Voltage

Safe Operating Area
Note

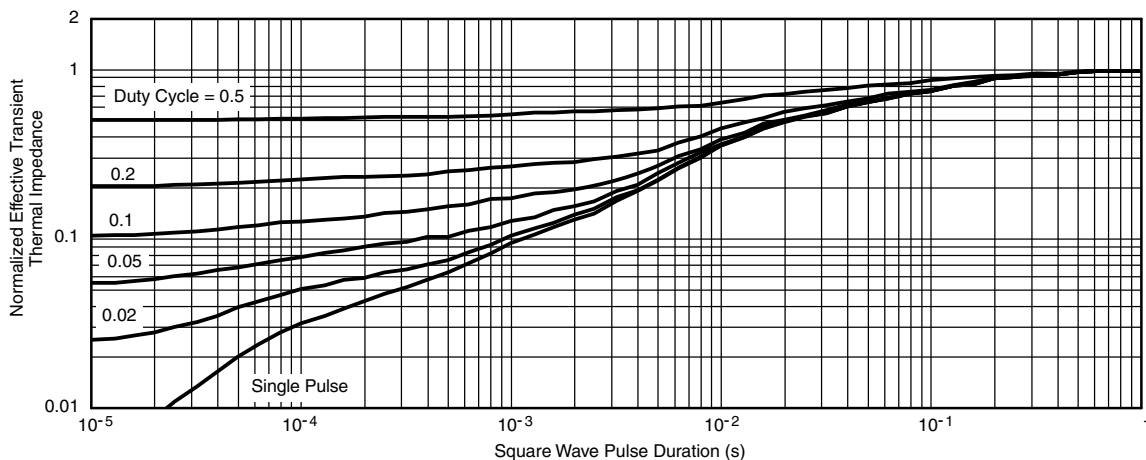
- a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63658.



PowerPAK® SO-8L Case Outline 2





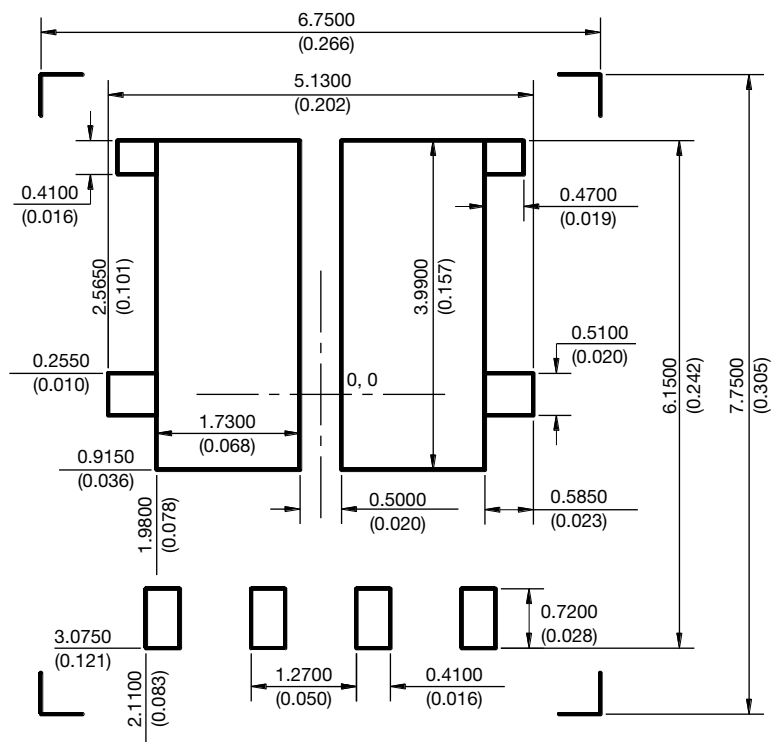
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.094			0.004		
b4	0.47			0.019		
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
e	1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	6.05	6.22	6.40	0.238	0.245	0.252
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.51			0.020		
W	0.23			0.009		
W1	0.41			0.016		
W2	2.82			0.111		
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°
ECN: C23-1026-Rev. D, 25-Sep-2023 DWG: 6044						

Note

- Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads
Dimensions in mm (inches)
Keep-out 6.75 (0.266) x 7.75 (0.305)



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